Rectifier diodes ultrafast

BYW29F series

GENERAL DESCRIPTION

Glass passivated high efficiency rectifier diodes in full pack, plastic envelopes, featuring low forward voltage drop, ultra-fast recovery times and soft recovery characteristic. They are intended for use in switched mode power supplies and high frequency circuits in general where low conduction and switching losses are essential.

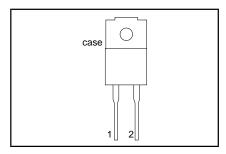
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{RRM} V _F I _{F(AV)} t _{rr}	BYW29F- Repetitive peak reverse voltage Forward voltage Forward current Reverse recovery time	100 100 0.895 8 25	150 150 0.895 8 25	200 200 0.895 8 25	V V A ns

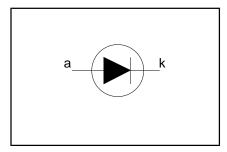
PINNING - SOD100

PIN	DESCRIPTION	
1	cathode	
2	anode	
case	isolated	

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V _{RRM} V _{RWM} V _R	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage		- - -	-100 100 100 100	-150 150 150 150	-200 200 200 200	V V
I _{F(AV)}	Average forward current ²	square wave; δ = 0.5; $T_{hs} \le 106$ °C sinusoidal; a = 1.57; $T_{hs} \le 109$ °C	-		8 7.3		A A
I _{F(RMS)} I _{FRM}	RMS forward current Repetitive peak forward current		-		11.3 16		A A
I _{FSM}	Non-repetitive peak forward current	t = 10 ms t = 8.3 ms sinusoidal; with reapplied	-		80 88		A A
$\begin{matrix} I^2t \\ T_{stg} \\ T_j \end{matrix}$	I ² t for fusing Storage temperature Operating junction temperature	V _{RWM(max)} t = 10 ms	- -40 -		32 150 150		A ² s °C °C

¹ $T_{hs} \le 141^{\circ}C$ for thermal stability.

² Neglecting switching and reverse current losses

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ISOLATION

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	Repetitive peak voltage from both terminals to external heatsink	R.H. ≤ 65% ; clean and dustfree	-	-	1500	V
C _{isol}	Capacitance from cathode to external heatsink	f = 1 MHz	-	12	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	mounting base Thermal resistance junction to	with heatsink compound without heatsink compound in free air	- - -	- - 55	5.5 7.2 -	K/W K/W K/W
	ambient					

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage	$I_F = 8 \text{ A}; T_i = 150^{\circ}\text{C}$	-	0.80	0.895	V
	_	$I_{\rm F} = 8 \text{A}$	-	0.92	1.05	V
		$I_{\rm F} = 20 \text{ A}$	-	1.1	1.3	V
I _R	Reverse current	$\dot{V}_R = V_{RWM}$; $T_i = 100 ^{\circ}C$	-	0.3	0.6	mA
		$V_R = V_{RWM}$	-	2	10	μΑ

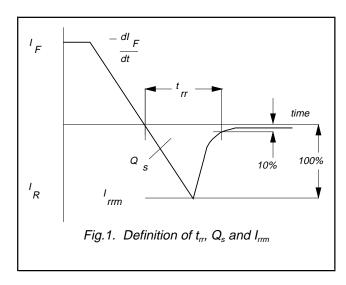
DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

]					
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Q _s		$I_F = 2 \text{ A}; V_R \ge 30 \text{ V}; -dI_F/dt = 20 \text{ A}/\mu\text{s}$	-	4	11	nC
t _{rr}	Reverse recovery time	I _F = 1 A; V _R ≥ 30 V; -dI _F /dt = 100 A/μs	-	20	25	ns
I _{rrm}	Peak reverse recovery current	$I_F = 10 \text{ A}; V_R \ge 30 \text{ V}; T_j = 100 ^{\circ}\text{C}; \\ -dI_F/dt = 50 \text{ A}/\mu\text{s}$	-	1	2	Α
V_{fr}	Forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A/}\mu\text{s}$	-	1	-	V

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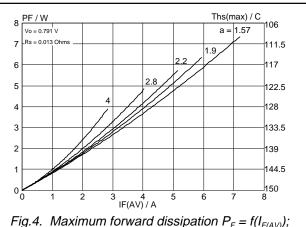
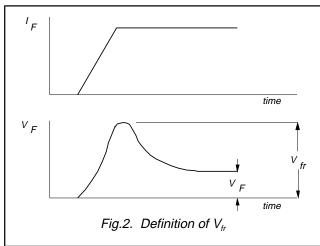
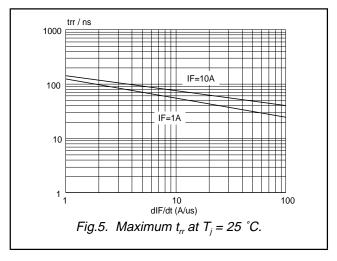
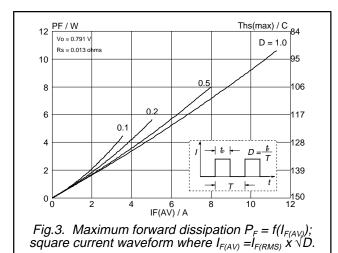
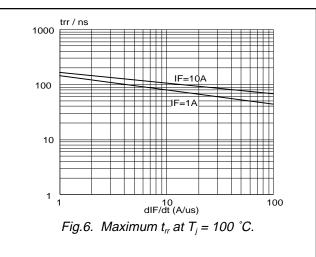


Fig.4. Maximum forward dissipation $P_F = f(I_{F(AV)})$; sinusoidal current waveform where a = form factor = $I_{F(RMS)} / I_{F(AV)}$.



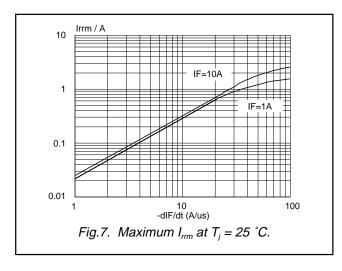


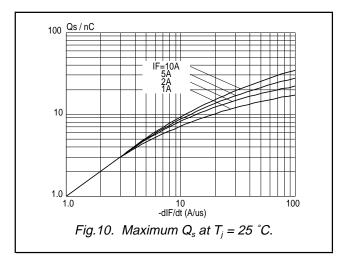


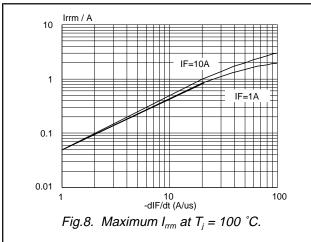


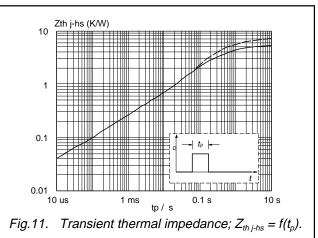
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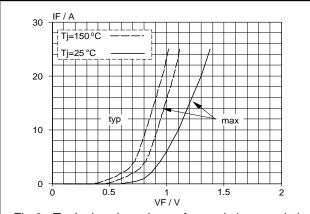
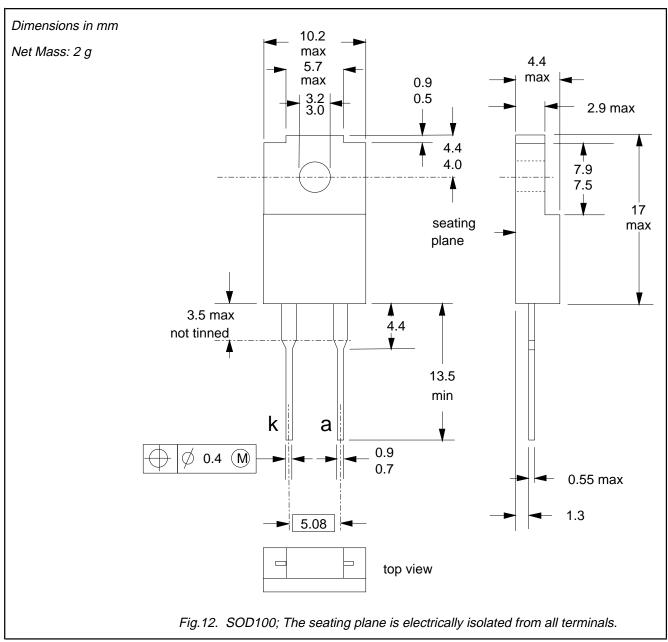


Fig.9. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_j

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MECHANICAL DATA



- Accessories supplied on request: refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification This data sheet contains preliminary data; supplementary data may be published later					
Product specification	This data sheet contains final product specifications.				
Limiting values					

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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